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Edited by:

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A 15 MHz – 600 MHz, 20 mW, 0.38 mm², Fast Coarse Locking Digital DLL in 0.13μm CMOS

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Abstract - A digital delay-locked-loop (DLL) suitable for generation of multiphase clocks in applications such as time-interleaved and pipelined ADCs locks in a very wide (40X) frequency range. The DLL provides 12 uniformly delayed phases that are free of false harmonic locking. The digital control loop has two stages: a fast-locking coarse acquisition is achieved in four cycles using binary search; a fine linear loop achieves low jitter (8.9 ps rms @ 600 MHz) and tracks PVT variations. The DLL consumes 20 mW and occupies a 470 μm X 800 μm area in 0.13μm CMOS.

I. INTRODUCTION

Time-interleaved and pipeline ADC's require generation of multiple clock phases in a very wide operating frequency range with challenging jitter requirements in the upper frequency range. DLLs are often used in these applications, but they face design tradeoffs between the requirements for low jitter, fast locking, wide frequency-range and low power. Low voltage headroom, associated with supply voltages in scaled technologies presents a challenge for analog control loops in a DLL to achieve a very wide locking range. This limitation is solved by using digital control loops that ideally can use longer wordlengths to extend the dynamic locking range [1-11]. Jitter in digital DLL's is determined by the size of the DAC LSB that controls the delay line. However, the interaction of the wide dynamic range control with the delay line dramatically impacts other performance metrics such as the locking time, jitter, power consumption and silicon area.

In this DLL, a novel architecture allows the design to achieve 40X locking range together with fast locking, and low jitter at high frequencies in steady state. This locking range enables a wide set of operating modes as well as the testability of the ADC system that uses it. A 10-bit digital control is used to control the jitter, and the locking range. It is used to adjust the delay of the current-starved inverter based delay line, where the 4 most significant bits (MSB's)

coarsely select the frequency range (15MHz – 600MHz) using a fast binary search, and a binary-weighted DAC replicated at each delay cell. The 6 least significant bit (LSB's) linearly control the delay elements for a low jitter in steady state. The unit-element LSB DAC is share among all delay cells. This split-control architecture enable the delay adjustment of delay elements with low supply voltage in the desired operating range. This design also allows for low power consumption and a moderate silicon area for a DLL with 12 clock phases.

II. ARCHITECTURE

Figure 1 shows the basic block diagram of the proposed DLL. The binary search brings the total delay D of the delay line within the locking range, $3T/4 < D < 5T/4$. If $3T/4 < D$, the UNDER signal is activated by the false-locking detection logic, Table 1.

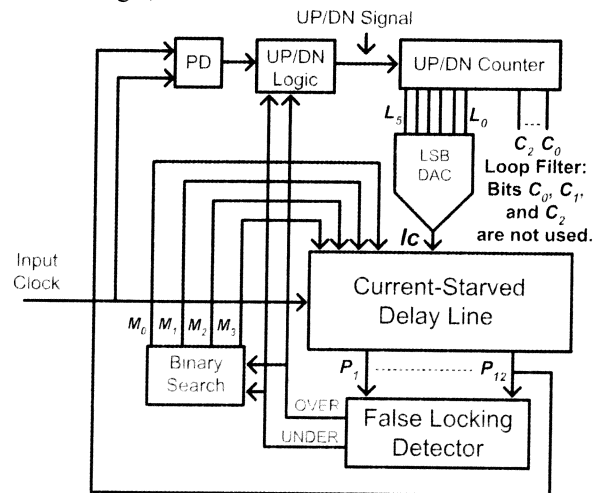


Fig. 1: Block diagram of the DLL.

In the prototype chip, the MSB and LSB currents are programmable, which gives flexibility for testing purposes. This also allows adjusting the LSB current to minimize the jitter at lower frequencies.

Replicating the MSB DAC across all the current starved inverters minimized DC current consumption, as only the dynamic current is drawn from these DACs. On the other hand, the LSB DAC current was mirrored to all current cells, since it is much smaller. The DC current in the LSB's corresponds to only the lower 6 LSBs of the total 10 bits in the dual digital control loop; furthermore, current scaling by a factor of 20 lowers the mirrored DC current. This current is scaled up to its nominal value locally at each delay cell where only the dynamic power is consumed.

III. IMPLEMENTATION AND TESTING

The DLL has been implemented in a general-purpose, 0.13 μ m 6M1P CMOS technology. The DLL occupies 470 μ m \times 800 μ m area. Measured jitter performance is summarized in Table 2 and jitter measurement plot at 600 MHz and 380 MHz are shown in Fig. 3 and Fig. 4, respectively. Five chips were tested with almost the same measurement results. The DLL clock is driven off-chip using LVDS pads, which worsens the jitter by up to 7 ps rms. The actual on-chip DLL jitter variance is expected to be up to (7 ps)² better than the squared of the rms values in Table 2. This expected on-chip jitter is also reported in Table 2. The linear control loop can be left running to absorb PVT variations in the locked state. The steady-state jitter produced by the LSB toggling is reduced with increased clock frequency as indicated in Eqn. (4). For frequencies larger than 300 MHz, the jitter produced by the LSB toggling is lower than the intrinsic jitter induced by the electronic noise. At low frequencies, however, the effect of the LSB toggling is higher, as the output will toggle between two phases as shown in Fig. 5. In the worst case, if the edge of the delayed clock gets very close to the input clock, the intrinsic jitter will make the linear loop to toggle between 3 LSBs producing a 3 edge clock eye diagram. As a result, the peak-to-peak jitter can be as big as 2 LSBs. This case is illustrated in the measured eye diagram of Fig. 6.

TABLE 2: RMS JITTER ACROSS THE OPERATING RANGE.

Freq. (MHz)	600	500	400	300	200	150	50	15
Measured rms off-chip jitter [ps]	8.9	8.9	9	9.5	10.2	20.5	100	116 ¹
Expected on-chip jitter [ps]	4.1	4.5	5	5.7	7.4	19.2	100	116

¹ An LSB current that is lower than in the other measurements was used here to improve the jitter.

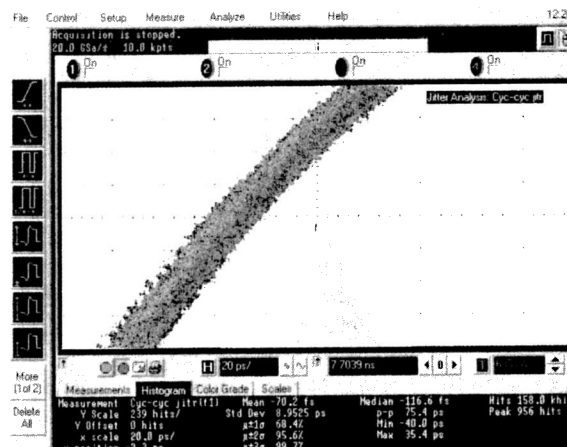


Fig. 3: Jitter measurement at 600 MHz.

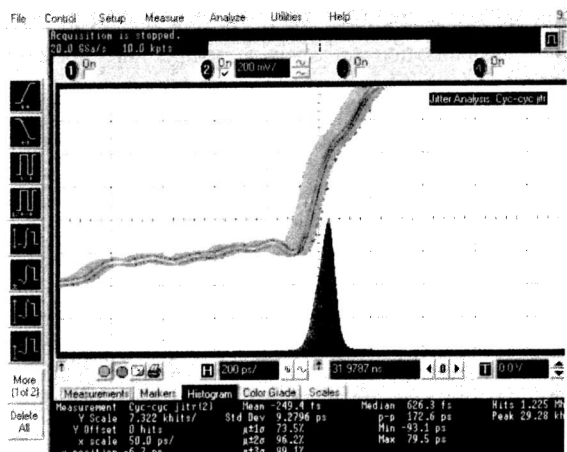


Fig. 4: Jitter measurement at 380 MHz.

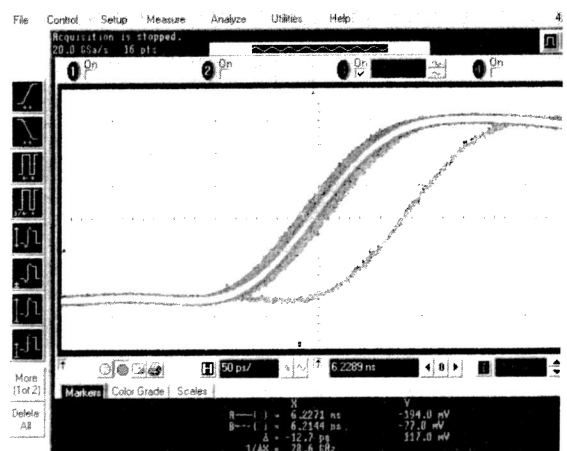


Fig. 5: Toggling of the LSB current for low frequency operation. The locking frequency is 15 MHz.

TABLE 3: COMPARISON BETWEEN THIS WORK AND RECENTLY REPORTED DLL S

	Tokun.[1]	Song[2]	Kim[3]	Kim[5]	Wang [6]	Bhor.[8]	Wang [9]	Yang[10]	Chang[11]	This work
Freq. (MHz)	20-300 (15X)	30-200 (6X)	40-800 (20X)	120MHz-1.8 GHz (15X)	400- 600(1.5X)	200-1.2G (6X)	150-550 (3.7X)	40-500 (13.75X)	2-700 (350X)	15-600 (40X)
VDD	2 – 4 V	2.5 V	1.2 V	3.3 V	2.4-3.3 V	1.2 V	1 V	1.8 V	1.4-2.5 V	1.2 V
Power	9 mW	30 mW	43 mW	86.6 mW	9.9 mW	6.1mW	0.37 mW	12.6 mW	23 mW	20 mW
Type	Analog	Digital	Digital	Digital	Digital	Digital	Digital	Digital	Digital	Digital
Area	0.03 mm ²	0.66 mm ²	0.22 mm ²	0.07 mm ²	0.7 mm ²	0.24 mm ²	0.0119 mm ²	0.2 mm ²	0.88 mm ²	0.38 mm ²
Jitter (rms)	6.9ps@ 200 MHz	7.1 ps 200 MHz	1.6 ps @ 700 MHz	1.8 ps @ 700 MHz	24.4 ps peak-to-peak	4.6 ps	5.5 peak-to- peak	1.5 ps	17.6 ps peak-to-peak	8.9ps @ 600 MHz
Locking time	1.8 μ s	-	-	1 cycles	10 cycles	-	4 cycles	134-14 cycles	32 cycles	4 cycles coarse lock
CMOS	0.30 μ m	0.25 μ m	0.13 μ m	0.35 μ m	0.35 μ m	0.13 μ m	65 nm	0.18 μ m	0.18 μ m	0.13 μ m

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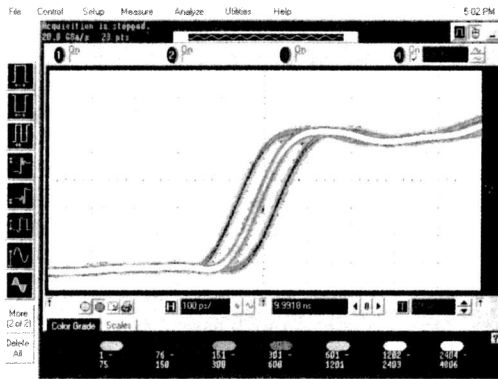


Fig. 6: Measured data showing the case of 3 LSBs flipping in the LSB DAC for low frequency operation. The locking frequency is 15 MHz.

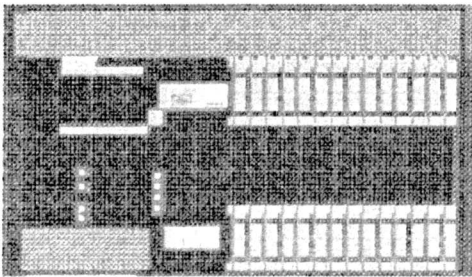


Fig. 7: Chip micrograph. DLL size is 470 μ m X 800 μ m.

IV. CONCLUSIONS

This paper presents an all digital implementation of a DLL with a 40X frequency locking range. A dual loop design, consisting in a coarse fast binary search combined with a linear search is proposed. This design achieves a large locking range with fast coarse locking while keeping the jitter and power consumption low. The chip occupies a 470 μ m X 800 μ m area and draws 20 mW @ 600 MHz in 0.13 μ m general-purpose CMOS. The 12 uniform phases of this DLL makes it suitable for providing the phases in applications such as time-interleaved and pipelined ADCs and broadband communications.